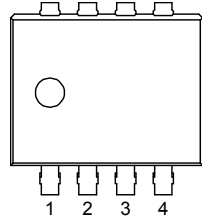
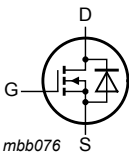


N-channel 100 V 71 mΩ standard level MOSFET in LFAK33 designed specifically for PoE applications

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$Q_{G(tot)}$	total gate charge	$V_{GS} = 10\text{ V}$; $I_D = 5\text{ A}$; $V_{DS} = 50\text{ V}$; $T_j = 25\text{ °C}$; Fig. 14 ; Fig. 15	-	16.4	-	nC
Avalanche Ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(init)} = 25\text{ °C}$; $I_D = 18\text{ A}$; $V_{sup} \leq 100\text{ V}$; $R_{GS} = 50\text{ }\Omega$; unclamped; Fig. 3	-	-	25	mJ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 LFAK33 (SOT1210)	 mbb076
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN075-100MSE	LFAK33	Plastic single ended surface mounted package (LFAK33); 4 leads	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN075-100MSE	M75E10

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 175\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	100	V

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Symbol	Parameter	Conditions		Min	Max	Unit
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _j = 25 °C; Fig. 1		-	18	A
		V _{GS} = 10 V; T _{mb} = 100 °C; Fig. 1		-	13	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; Fig. 4		-	74	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	65	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	54	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	74	A
Avalanche Ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 18 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; unclamped; Fig. 3		-	25	mJ

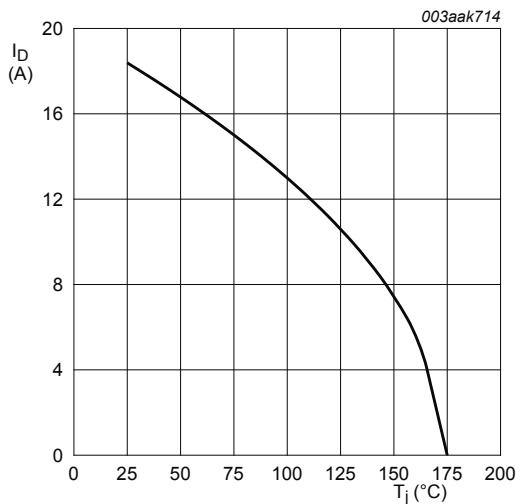


Fig. 1. Continuous drain current as a function of mounting base temperature

$V_{GS} \geq 10V$

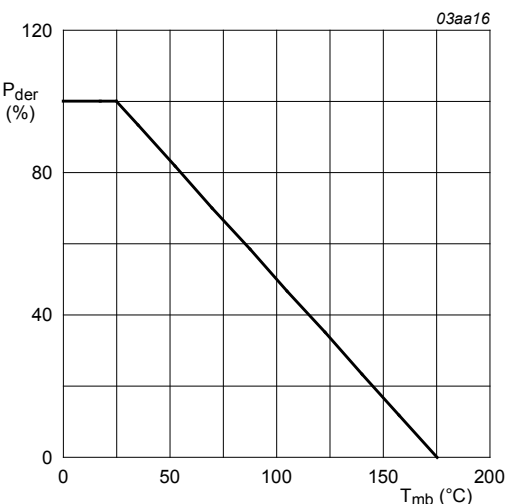


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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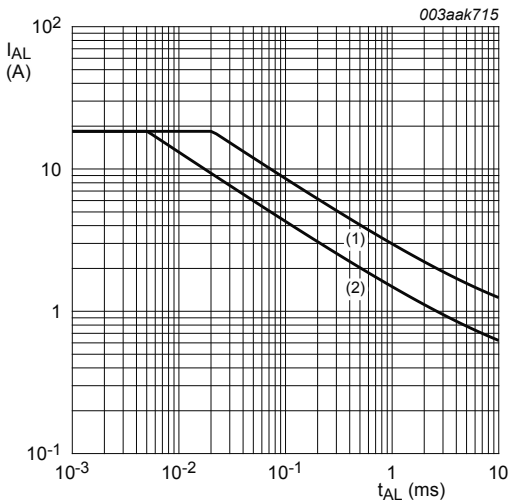


Fig. 3. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j(jnt)} = 25^{\circ}\text{C}$; (2) $T_{j(jnt)} = 100^{\circ}\text{C}$

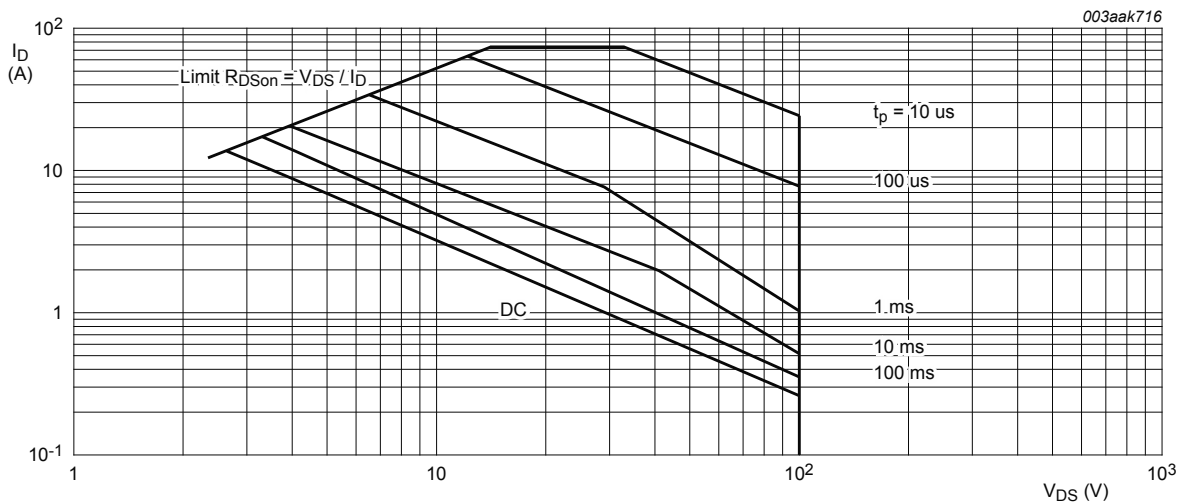


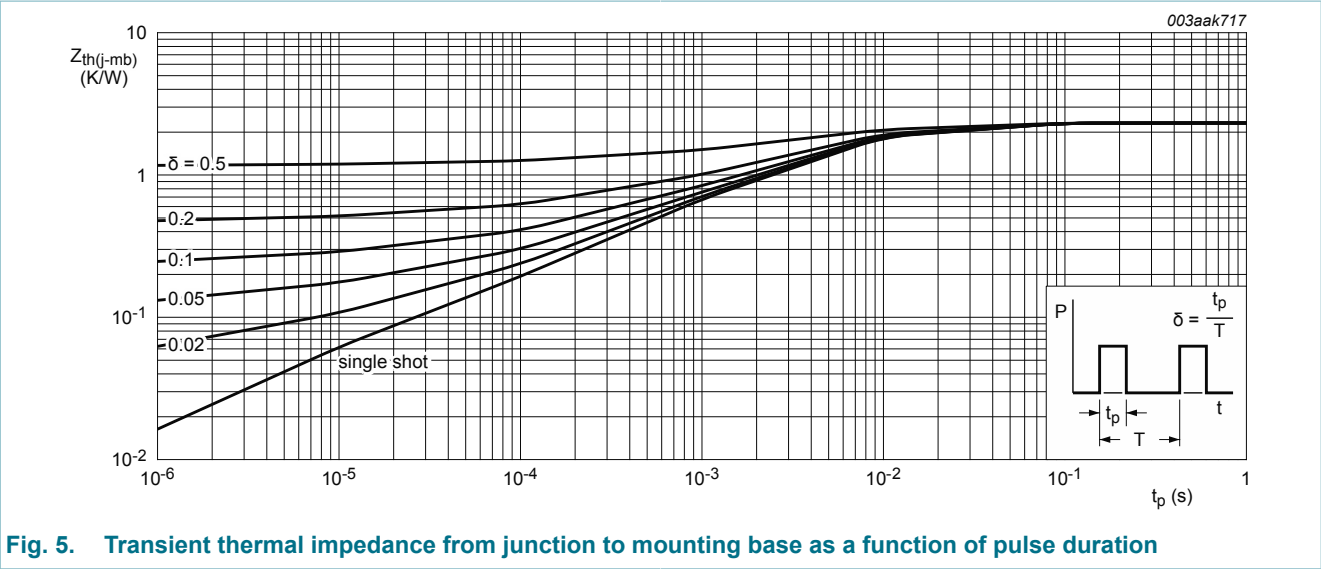
Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}\text{C}$; I_{DM} is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	2.09	2.32	K/W



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _J = 25 °C	100	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _J = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 25 °C; Fig. 10; Fig. 11	2.3	3.3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 175 °C; Fig. 10	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = -55 °C; Fig. 10	-	-	4.6	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _J = 25 °C	-	0.01	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _J = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _J = 25 °C	-	10	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _J = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 5 A; T _J = 25 °C; Fig. 12	-	57	71	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _J = 100 °C; Fig. 13; Fig. 12	-	-	128	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _J = 175 °C; Fig. 13; Fig. 12	-	-	192	mΩ
R _G	gate resistance	f = 10 MHz	-	1.55	-	Ω

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Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; Fig. 14 ; Fig. 15		-	16.4	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V; T _j = 25 °C		-	12.9	-	nC
Q _{GS}	gate-source charge	I _D = 5 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j = 25 °C; Fig. 14 ; Fig. 15		-	3.1	-	nC
Q _{GS(th)}	pre-threshold gate-source charge			-	2.1	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge			-	1	-	nC
Q _{GD}	gate-drain charge	I _D = 5 A; V _{DS} = 50 V; V _{GS} = 10 V; T _j 25 °C; Fig. 14 ; Fig. 15		-	5.3	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 5 A; V _{DS} = 50 V; T _j = 25 °C; Fig. 14 ; Fig. 15		-	4.3	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 16		-	773	-	pF
C _{oss}	output capacitance			-	66	-	pF
C _{rss}	reverse transfer capacitance			-	48	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; R _L = 10 Ω; V _{GS} = 10 V; R _{G(ext)} = 5 Ω; T _j = 25 °C		-	5.5	-	ns
t _r	rise time			-	5.8	-	ns
t _{d(off)}	turn-off delay time			-	12.4	-	ns
t _f	fall time			-	6.2	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 17		-	0.89	1.2	V
t _{rr}	reverse recovery time	I _S = 5 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 50 V; T _j = 25 °C		-	35.8	-	ns
Q _r	recovered charge			-	50.7	-	nC

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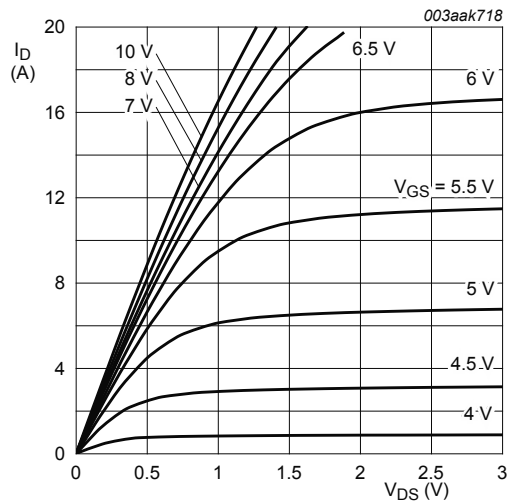


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

$T_j = 25^{\circ}\text{C}$

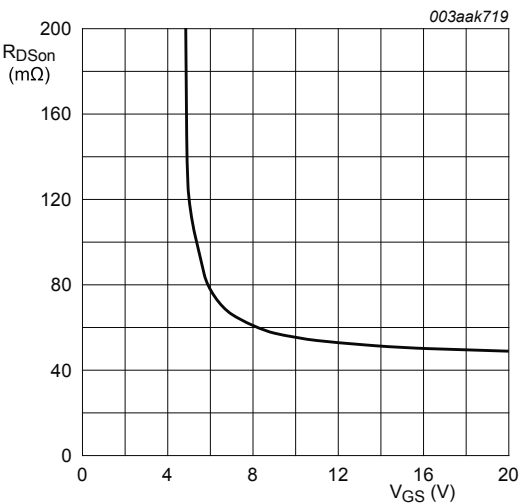


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^{\circ}\text{C}; I_D = 5\text{A}$

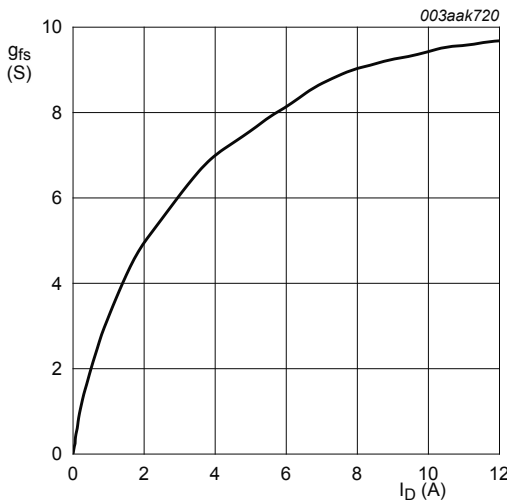


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25^{\circ}\text{C}; V_{DS} = 10\text{V}$

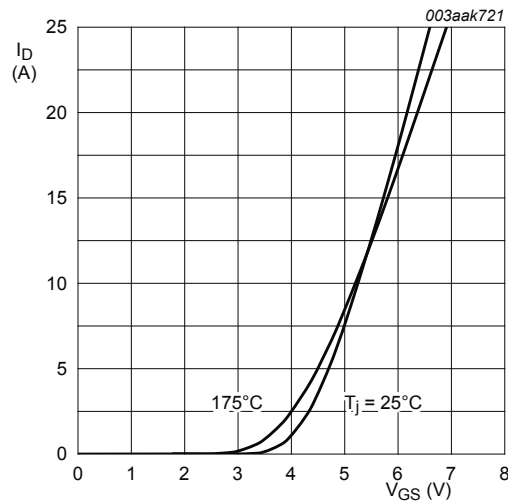


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{V}$

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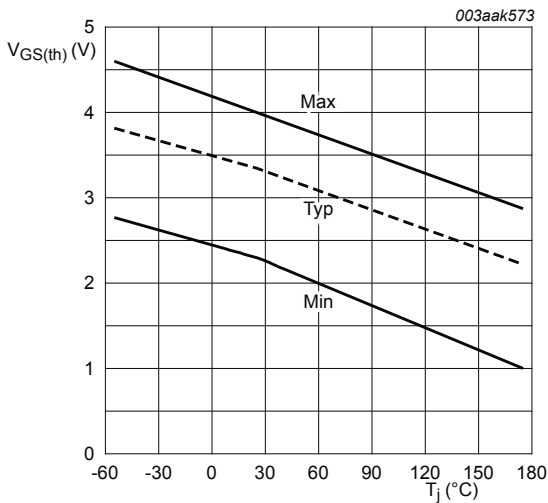


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

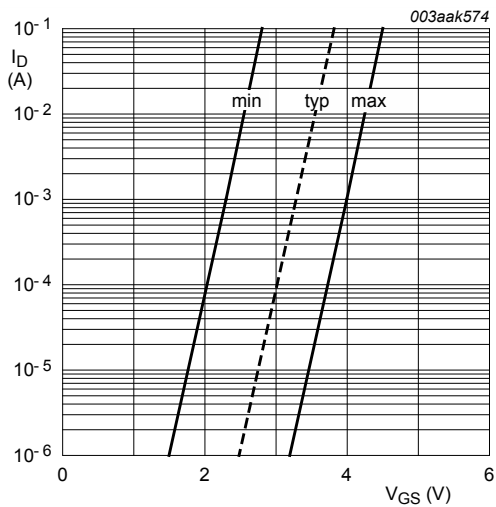


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\text{ °C}; V_{DS} = 5\text{ V}$

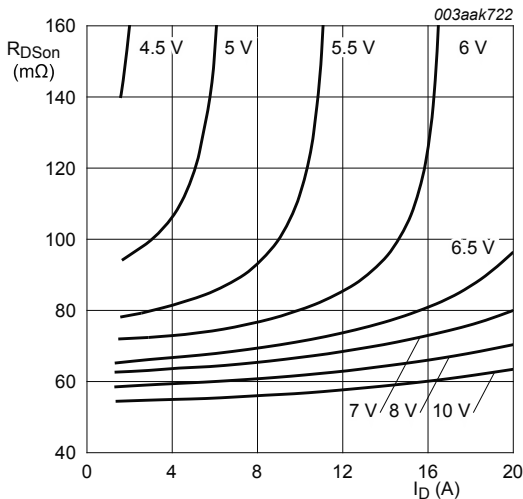


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25\text{ °C}$

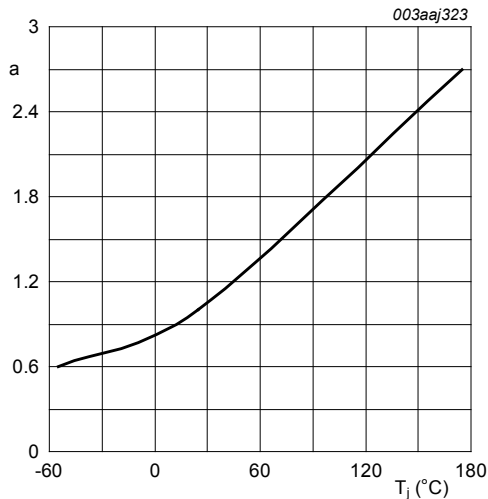


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25\text{ °C})}$$

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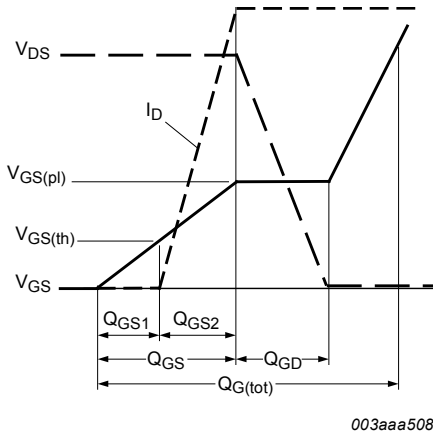


Fig. 14. Gate charge waveform definitions

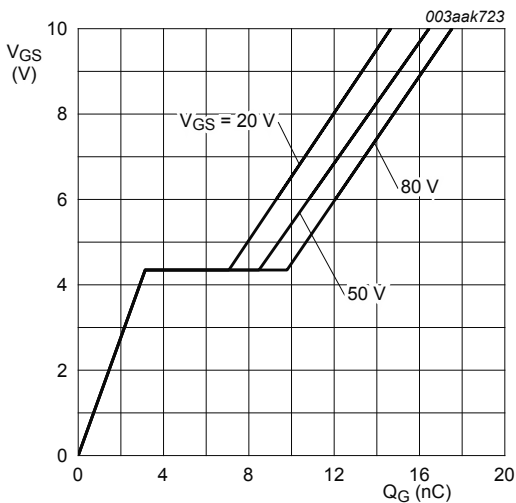


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25^{\circ}\text{C}; I_D = 5\text{ A}$

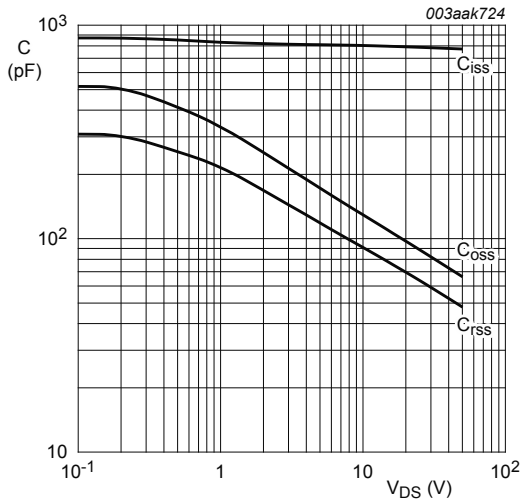


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

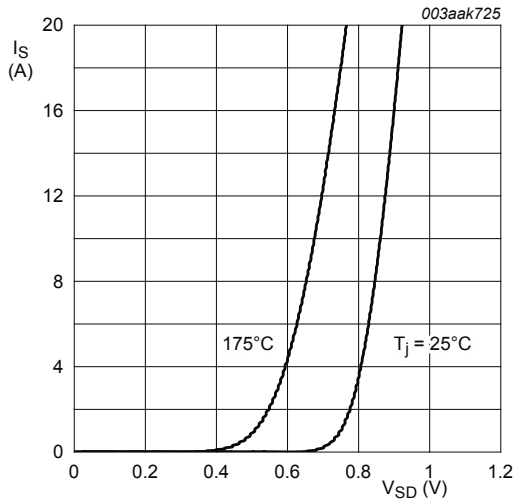


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{ V}$

11. Package outline

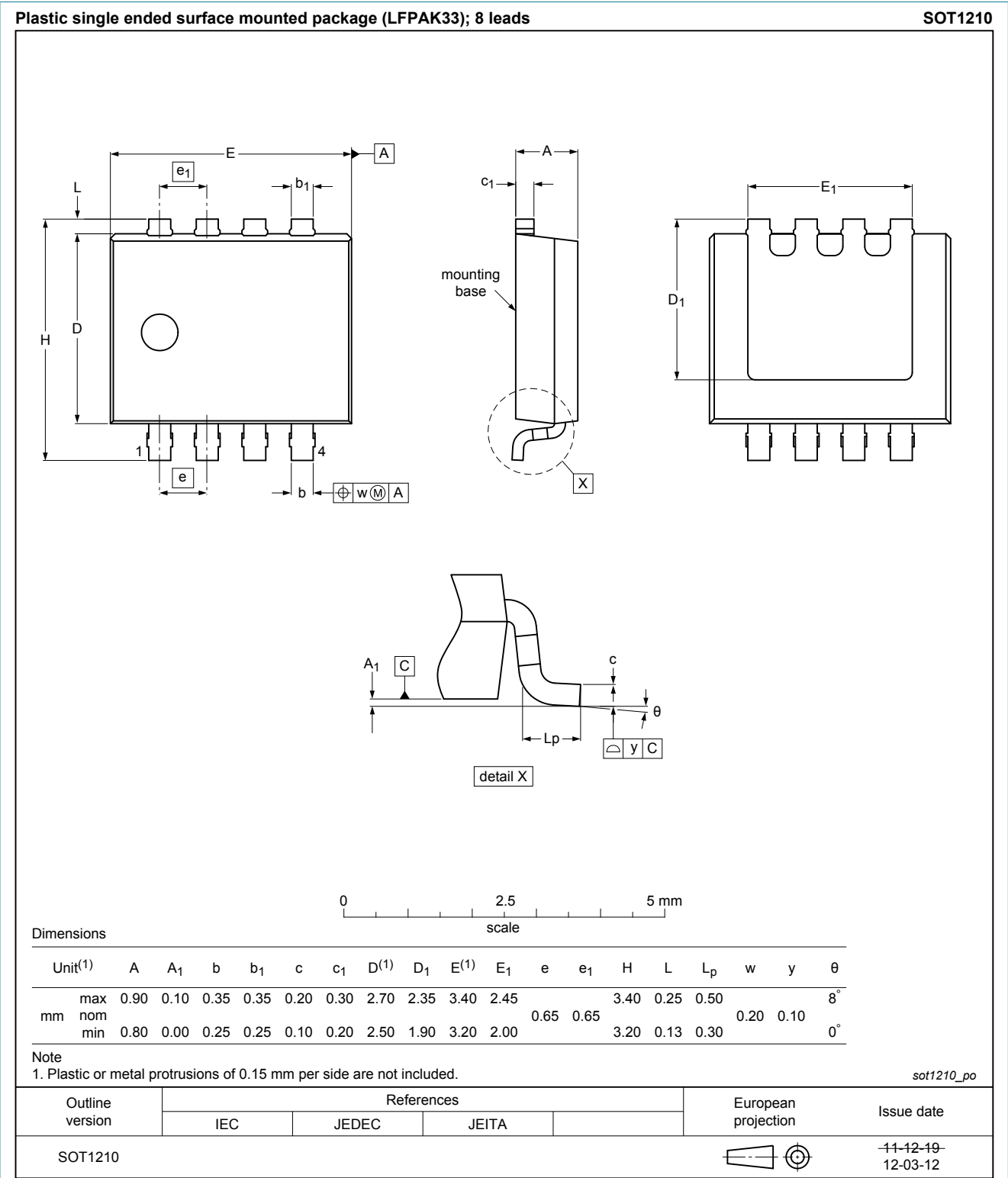


Fig. 18. Package outline LPAK33 (SOT1210)

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